CLAIMS

WHAT IS CLAIMED IS:

1. A blank mask comprising:

a transparent substrate; and

a light shielding film disposed on the transparent substrate,

wherein the light shielding film comprises a transition metal and at least one selected from the group consisting of oxygen and nitrogen,

wherein the light shielding film comprises a first light shielding layer and a second light shielding layer disposed on the first light shielding layer,

wherein the first light shielding layer comprises the transition metal in an amount of 40 to 50 at%,

wherein the second light shielding layer comprises the transition metal in an amount of 50 to 80 at%,

wherein the transition metal comprises Cr, and

wherein a Mtr value of Equation 1 below of a surface of the light shielding film is 6 or less:

[Equation 1]

Mtr = |Rsk|*Rku

where, in the Equation 1, |Rsk| is an absolute value of an Rsk value, which is a height skewness of the surface of the light shielding film, and Rku is kurtosis of the surface of the light shielding film, and wherein the Rku value is 6 or less.

2. The blank mask of claim 1, wherein the Rsk value is 1 or less.

3. The blank mask of claim 1, wherein a Dw value of Equation 2 below of the light shielding film is 0.01 % or less:

[Equation 2]

$$Dw = \frac{Ds - Do}{Do} \times 100\ (\%)$$

where, in the Equation 2, Ds is a weight of the blank mask measured after forming a photoresist film of 1300Å thickness on the light shielding film and removing the photoresist film, and Do is a weight of the blank mask measured before forming the photoresist film on the light shielding film.

4. The blank mask of claim 1, wherein a sum of an amount of the nitrogen and the oxygen in the second light shielding layer is 10 to 35 at%.

5. A photomask comprising:

a transparent substrate; and

a light shielding pattern film disposed on the transparent substrate,

wherein the light shielding pattern film comprises a transition metal and at least one selected from the group consisting of oxygen and nitrogen,

wherein the light shielding film comprises a first light shielding layer and a second light shielding layer disposed on the first light shielding layer,

wherein the first light shielding layer comprises the transition metal in an amount of 40 to 50 at%,

wherein the second light shielding layer comprises the transition metal in an amount of 50 to 80 at%,

wherein the transition metal comprises Cr, and

wherein a Mtr value of Equation 1 below of a surface of the light shielding pattern film is 6 or less:

[Equation 1]

Mtr = |Rsk|*Rku

where, in the Equation 1, |Rsk| is an absolute value of an Rsk value, which is a height skewness of the surface of the light shielding pattern film, and Rku is kurtosis of the surface of the light shielding pattern film, and wherein the Rku value is 6 or less.

6. The photomask of claim 5, wherein the Rsk value is 1 or less.